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(54) Title: INTEGRATED CAPACITORS IN PACKAGE-LEVEL STRUCTURES, PROCESSES OF MAKING SAME, AND SYSTEMS CONTAINING SAME

(57) Abstract: An article includes a top electrode that is embedded in a solder mask. An article includes a top electrode that is on a core structure. A process of forming the top electrode includes reducing the solder mask thickness and forming the top electrode on the reduced-thickness solder mask. A process of forming the top electrode includes forming the top electrode over a high-K dielectric that is in a patterned portion of the core structure.

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